L Number	Hits	Search Text	DB	Time stamp
-	28	dram and (capacitor or capacitive or	USPAT;	2004/09/07 09:40
		capacitance) near8 (aluminum adj nitride or	US-PGPUB;	
		aln or al adj n)	EPO; JPO;	
			DERWENT;	,
	_		IBM_TDB	
-	13	(dram or sdram or memory) and (capacitor or	USPAT;	2004/08/31 15:34
		capacitive or capacitance) near5 (dielectric	US-PGPUB;	
		or insulator or insulating) near5 (aluminum	EPO; JPO;	
		adj nitride or aln or al near2 n or al2n3)	DERWENT;	
_	23	(dram or sdram or memory) and (capacitor or	IBM_TDB USPAT;	2004/08/31 15:35
	23	capacitive or capacitance) near5 (dielectric	US-PGPUB;	2004/08/31 15:35
		or insulator or insulating) near5 (aluminum	EPO; JPO;	
		near3 nitride or aln or al near2 n or al2n3)	DERWENT;	
		,	IBM TDB	
-	23	(dram or sdram or memory) and (capacitor or	USPAT;	2004/08/31 15:39
		capacitive or capacitance) near5 (dielectric	US-PGPUB;	
		or insulator or insulating or spacer) near5	EPO; JPO;	
		(aluminum near3 nitride or aln or al near2 n	DERWENT;	
		or al2n3)	IBM_TDB	
-	15	("5183684" "5356608" "5573742"	USPAT	2004/08/31 15:38
		"5599732" "5605858" "5650361"		
		"5656113" "5687112" "5709928"		
		"5767578" "5773882" "5783483"		
	67	"5783716" "5786259" "5786635").PN.	HCDAG	2004/00/22 25 :-
-	6/	(capacitor or capacitive or capacitance or storage) near5 (dielectric or insulator or	USPAT;	2004/08/31 15:41
		insulating or spacer) near5 (aluminum near3	US-PGPUB;	
		nitride or aln or al near2 n or al2n3)	EPO; JPO; DERWENT;	
		mittide of aim of ai hearz in or arzhs,	IBM TDB	
-	75	(capacitor or capacitive or capacitance or	USPAT;	2004/08/31 16:21
	, 3	storage) near5 (dielectric or insulator or	US-PGPUB;	2004,00,31 10.21
		insulating or spacer) near5 (aluminum near3	EPO; JPO;	
		nitride or alm or al near2 m or al2m3 or	DERWENT;	
ļ		nitride near3 Al)	IBM_TDB	
-	64		USPĀT;	2004/08/31 16:22
ļ		storage) near5 (dielectric or insulator or	US-PGPUB;	
		insulating or spacer) near5 (metal near2	EPO; JPO;	
		nitride)	DERWENT;	
	000	257/210 colo	IBM_TDB	0004/00/07 55 55
-	898	257/310.ccls.	USPAT;	2004/09/01 08:50
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	110	257/310.ccls. and (aluminum near3 nitride or	USPAT;	2004/09/01 08:51
		al near3 nitride or alm or al near2 m or	US-PGPUB;	
		"al2n3")	EPO; JPO;	
			DERWENT;	
ļ			IBM_TDB	
-	111	257/310.ccls. and (aluminum near3 nitride or	USPĀT;	2004/09/01 08:52
		al near3 nitride or aln or al near2 n or	US-PGPUB;	
		"al2n3" or alno or alon or aluminum near3	EPO; JPO;	
		oxynitride or nitrided near2 alumina)	DERWENT;	
		0557/010	IBM_TDB	
~	111	257/310.ccls. and (aluminum near3 nitride or	USPAT;	2004/09/01 09:40
		al near3 nitride or aln or al near2 n or	US-PGPUB;	
		"al2n3" or alno or alon or aluminum near3 oxynitride or nitrided near2 alumina or	EPO; JPO;	
		nitride near alumina)	DERWENT;	
_	14	("4455568" "5032892" "5079609"	IBM_TDB USPAT	2004/09/01 09:11
	_4	"5212402" "5266821" "5366931"	USFAI	2004/03/01 03:11
		"5656834"		
		"5940676" "5955758" "5972791"		
		"5973908" "6034391").PN.		
-	1576	(dram or sdram or memory) and (insulator or	USPAT;	2004/09/01 09:42
	_	insulating or dielectric) near6 ((aluminum	US-PGPUB;	,,
		or alumina or al) near4 (nitride or n or	EPO; JPO;	
}		nitrided or oxynitride) or aln)	DERWENT;	
			IBM TDB	1

,				
-	320	(dram or sdram) and (insulator or insulating	USPAT;	2004/09/01 09:43
		or dielectric) near5 ((aluminum or alumina or al) near3 (nitride or n or nitrided or	US-PGPUB;	
		or all hears (hitride or h or hitrided or oxynitride) or aln)	EPO; JPO;	
		oxymitride, or aim,	DERWENT;	
1_	36	(dram or sdram) and (insulator or insulating	USPAT;	2004/09/01 10:26
		or dielectric) near5 ((aluminum or alumina	US-PGPUB;	2004/05/01 10:20
		or al) near3 (nitride or n or nitrided or	EPO; JPO;	
		oxynitride) or aln) near15 (capacitor or	DERWENT;	
		capacitive or capacitance)	IBM TDB	
-	14		USPAT;	2004/09/01 10:37
		6358810.pn. 5183684.pn. 6372530.pn.	US-PGPUB;	
		6072211.pn.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	257/68.ccls. and (insulator or insulating or	USPAT;	2004/09/01 10:39
		spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
-		oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	IBM_TDB	
_	6		USPAT;	2004/09/01 10:41
		spacer or dielectric) near8 ((aluminum or	US-PGPUB;	2004/03/01 10:41
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
	1	nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
		aln or al2n3 or alon or alno or alxny)	_	
-	76	,	USPAT;	2004/09/01 11:56
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	IBM_TDB	
_	5		USPAT	2004/09/01 11:05
		"6531750" "6548871").PN.	OSFAI	2004/05/01 11:05
-	10		USPAT;	2004/09/01 11:58
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
	1.2	aln or al2n3 or alon or alno or alxny)		
-	13	257/300.ccls. and (insulator or insulating	USPAT;	2004/09/01 12:08
		or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or	US-PGPUB; EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM TDB	
		aln or al2n3 or alon or alno or alxny)		
-	15	5977582.URPN.	USPAT	2004/09/01 12:05
-	16	257/301.ccls. and (insulator or insulating	USPAT;	2004/09/01 12:17
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	IBM_TDB	
_	8		USPAT;	2004/09/01 12:19
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	2004/03/01 12:19
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
		aln or al2n3 or alon or alno or alxny)	_	
-	22	,	USPAT;	2004/09/01 12:22
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or	DERWENT;	
		aln or al2n3 or alon or alno or alxny)	IBM_TDB	
-	12	257/304.ccls. and (insulator or insulating	USPAT;	2004/09/01 12:46
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
	L	aln or al2n3 or alon or alno or alxny)		

	· · · · · · · · · · · · · · · · · · ·		···	
-	6	257/305.ccls. and (insulator or insulating	USPAT;	2004/09/01 12:47
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or	DERWENT;	
		aln or al2n3 or alon or alno or alxny)	IBM_TDB	
_	66		USPAT;	2004/09/01 13:05
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	2004/09/01 13:05
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
	1	nitrate or n or oxynitride or oxinitride or	DERWENT;	
	Ì	oxy-nitride or nitridation or nitrdation) or	IBM TDB	
		aln or al2n3 or alon or alno or alxny)	12132	
-	8	1	USPAT;	2004/09/01 13:08
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	=====================================
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
	ŀ	nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM TDB	
		aln or al2n3 or alon or alno or alxny)	_	
-	50	257/532.ccls. and (insulator or insulating	USPAT;	2004/09/01 13:10
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
		aln or al2n3 or alon or alno or alxny)		
-	120	,	USPAT;	2004/09/07 10:18
		(capacitor or capacitance or capacitive)	US-PGPUB;	
	1	near8 (dielectric or insulator or insulating	EPO; JPO;	
	1	or spacer or insulative) near8 (alumina or	DERWENT;	
		aluminum near2 oxide or al near2 o or alo or	IBM_TDB	
	1	aluminum near nitride or al near2 n or aln)		2221/22/22 22 22
_	15	("5183684" "5356608" "5573742"	USPAT	2004/09/07 09:59
		"5599732" "5605858" "5650361" "5656113" "5687112" "5709928"		
ļ		"5656113" "5687112" "5709928" "5767578" "5773882" "5783483"		
		"5783716" "5786259" "5786635").PN.		
_	61	memory near8 (capacitor or capacitance) and	USPAT;	2004/09/07 14:14
		(capacitor or capacitance or capacitive)	US-PGPUB;	2004/03/07 14:14
		near8 (dielectric or insulator or insulating	EPO; JPO;	
		or spacer or insulative) near8 (metal near2	DERWENT;	
		nitride)	IBM TDB	
-	4	("4058430" "4861417" "5166092"	USPAT	2004/09/07 10:30
		"5256244").PN.		, ,
-	81	(capacitor or capacitance) near3 (dielectric	USPAT;	2004/09/07 15:13
		or insulator or diel or insulating or	US-PGPUB;	
		insulative or ins or spacer or gap) near10	EPO; JPO;	
		(aluminum near3 nitride or aln or al near2	DERWENT;	
		n)	IBM_TDB	
-	8	("5525542" "5578523" "5652176"	USPAT	2004/09/07 14:25
]	"5674771" "5734177" "5812364"		
_		"6255187" "6329234").PN.		0004/05/55
	1	"5789320".PN.	USPAT	2004/09/07 14:32
-	29	US-5656113-\$.DID. OR US-5709928-\$.DID. OR	USPAT;	2004/09/07 15:15
		US-5605858-\$.DID. OR US-5687112-\$.DID. OR	US-PGPUB;	
		US-5767578-\$.DID. OR US-5773882-\$.DID. OR	EPO; JPO;	
		US-5783483-\$.DID. OR US-5783716-\$.DID. OR	DERWENT;	
)		US-5786635-\$.DID. OR US-5786259-\$.DID. OR US-5183684-\$.DID. OR US-5356608-\$.DID. OR	IBM_TDB	
1		US-5573742-\$.DID. OR US-5599732-\$.DID. OR		
		US-5650361-\$.DID.		
_ i	4	6294420.pn. 6307775.pn.	USPAT;	2004/09/07 15:23
			US-PGPUB;	2004/03/07 15:23
			EPO; JPO;	
	l i		DERWENT;	
1			IBM TDB	
-	2	6358810.pn.	USPAT;	2004/09/07 15:37
]		-	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	6	6181056.pn. 6218771.pn. 6459096.pn.	USPAT;	2004/09/07 15:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	6072211.pn.	USPAT;	2004/09/07 15:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	6218293.pn.	USPAT;	2004/09/07 15:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	